DHG10C600PB

Sonic Fast Recovery Diode

V_{RRM}	=	600 V
I _{fav}	<i>=</i> 2x	5 A
t _{rr}	=	35 ns

preliminary

High Performance Fast Recovery Diode Low Loss and Soft Recovery **Common Cathode**

Part number

DHG10C600PB



Package: TO-220

RoHS compliant

• Industry standard outline

• Epoxy meets UL 94V-0

Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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Fast Dio	Fast Diode				Ratings	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ing voltage	$T_{VJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			600	V
I _R	reverse current, drain current	$V_{R} = 600 V$	$T_{VJ} = 25^{\circ}C$			10	μA
		$V_{R} = 600 V$	$T_{vJ} = 125^{\circ}C$			1	mA
V _F	forward voltage drop	I _F = 5 A	$T_{vJ} = 25^{\circ}C$			2.21	V
		$I_{F} = 10 \text{ A}$				3.07	V
		$I_F = 5 A$	T _{vJ} = 125°C			2.17	V
		$I_{F} = 10 \text{ A}$				3.13	V
	average forward current	T _c = 105°C	T _{vJ} = 150°C			5	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		$T_{vJ} = 150$ °C			1.14	V
r _F	slope resistance } for power lo	oss calculation only				185	mΩ
R _{thJC}	thermal resistance junction to case	e				3.15	K/W
R _{thCH}	thermal resistance case to heatsir	nk			0.50		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			40	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_{R} = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			40	Α
C	junction capacitance	V_{R} = 400 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		3		pF
I _{RM}	max. reverse recovery current)	$T_{vJ} = 25 °C$		2		Α
		$I_{\rm F} = 5 {\rm A}; V_{\rm R} = 400 {\rm V}$	T _{vJ} = °C		tbd		А
t _{rr}	reverse recovery time	$\begin{cases} I_{F} = 5 \text{ A}; V_{R} = 400 \text{ V} \\ -di_{F} / dt = 100 \text{ A} / \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		35		ns
)	T _{vJ} = °C		tbd		ns

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Package TO-220			Ratings			
Symbol	Definition	Conditions	min	typ.	max.	Unit
I _{RMS}	RMS current	per terminal "			35	Α
T_{vJ}	virtual junction temperature		-5	5	150	°C
T _{op}	operation temperature		-5	5	125	°C
T _{stg}	storage temperature		-5	5	150	°C
Weight				2		g
M _D	mounting torque		0.4	1	0.6	Nm
F _c	mounting force with clip		2)	60	Ν





Part description

- D = Diode
- H = Sonic Fast Recovery Diode
- G = extreme fast
- 10 = Current Rating [A] C = Common Cathode
- 600 = Reverse Voltage [V] PB = TO-220AB (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG10C600PB	DHG10C600PB	Tube	50	505294

Equivalent Circuits for Simulation		* on die level	$T_{VJ} = 150 \ ^{\circ}C$	
)[R	Fast Diode		
V _{0 max}	threshold voltage	1.14		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	182		mΩ

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2x e

A2

Dim.	Millimeter		Incl	nes
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
е	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



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